

ADVANCED INFORMATION

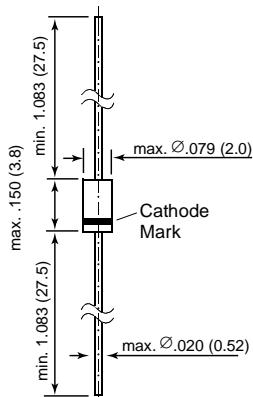
BAW75, BAW76

SMALL SIGNAL DIODES

FEATURES

- ◆ Silicon Epitaxial Planar Diode
- ◆ Fast switching diode.

DO-35



MECHANICAL DATA

Case: DO-35 Glass Case

Weight: approx. 0.13 g

Dimensions in inches and (millimeters)

MAXIMUM RATINGS

Ratings at 25°C ambient temperature unless otherwise specified.

		SYMBOL	VALUE	UNIT
Reverse Voltage BAW75 BAW76	VR	25	Volts	
	VR	50	Volts	
Peak Reverse Voltage BAW75 BAW76	V _{RM}	35	Volts	
	V _{RM}	75	Volts	
Rectified Current (Average) Half Wave Rectification with Resist. Load at T _A = 25 °C and f ≥ 50 Hz	I ₀	150 ¹⁾	mA	
Surge Forward Current at t < 1μs and T _j = 25°C	I _{FSM}	2	Amps	
Power Dissipation at T _A = 25°C	P _{tot}	500 ¹⁾	mW	
Junction Temperature	T _j	200	°C	
Storage Temperature Range	T _s	- 65 to +200	°C	

NOTES

(1) Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.

BAW75, BAW76

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

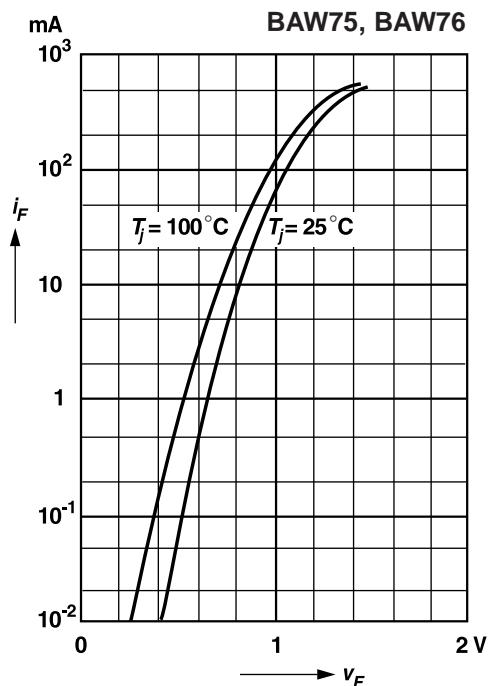
		<i>SYMBOL</i>	<i>MIN.</i>	<i>MAX.</i>	<i>UNIT</i>
Forward Voltage at $I_F = 30 \text{ mA}$ at $I_F = 100 \text{ mA}$	BAW75	V_F	—	1	V
	BAW76	V_F	—	1	V
Leakage Current at $V_R = 25 \text{ V}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 50 \text{ V}$ at $V_R = 50 \text{ V}, T_j = 150^\circ\text{C}$	BAW75	I_R	—	100	nA
	BAW75	I_R	—	100	μA
	BAW76	I_R	—	100	nA
	BAW76	I_R	—	100	μA
Reverse Breakdown Voltage Tested with 5 μA Pulses	BAW75	$V_{(BR)R}$	35	—	V
	BAW76	$V_{(BR)R}$	75	—	V
Capacitance at $V_F = V_R = 0 \text{ V}$	BAW75	C_{tot}	—	4	pF
	BAW76	C_{tot}	—	2	pF
Reverse Recovery Time from $I_F = 10 \text{ mA}$ through $I_R = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$ from $I_F = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$		t_{rr}	—	4	ns
		t_{rr}	—	2	ns
Thermal Resistance Junction to Ambient Air		$R_{\Theta JA}$	—	0.35 ¹⁾	K/mW

NOTES:

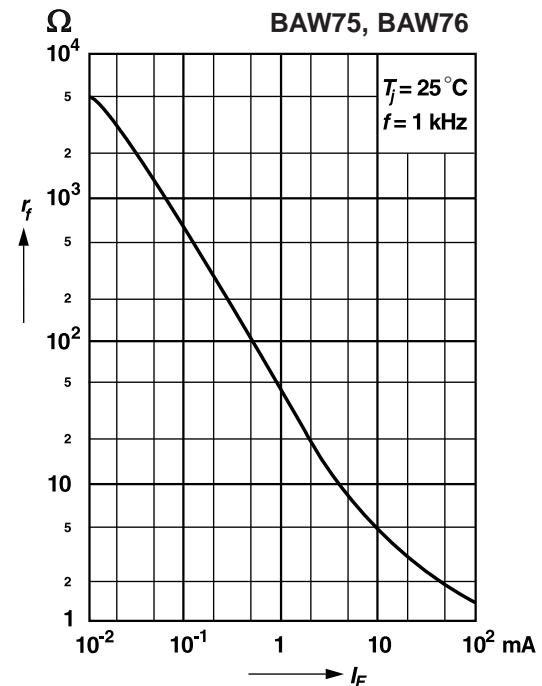
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RATINGS AND CHARACTERISTICS CURVES BAW75, BAW76

Forward characteristics

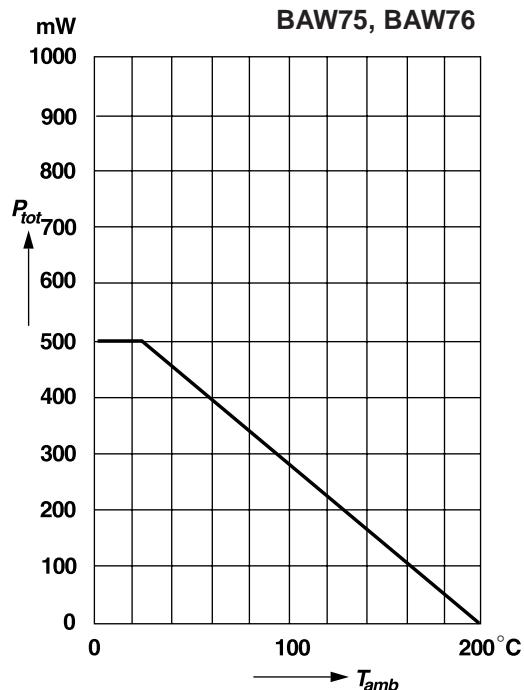


Dynamic forward resistance
versus forward current

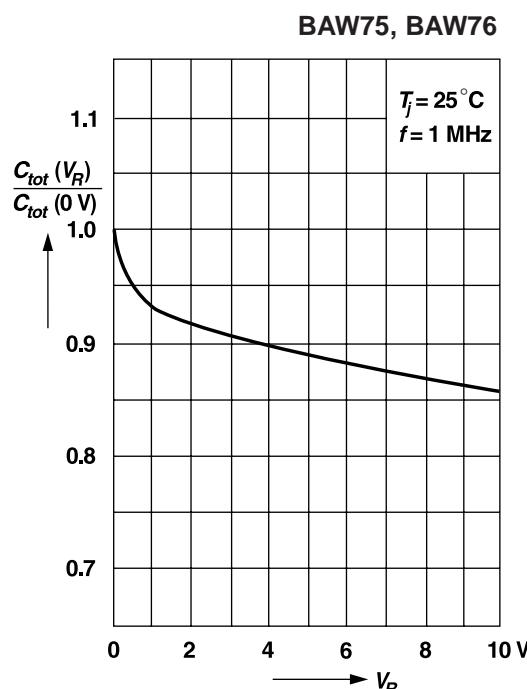


Admissible power dissipation
versus ambient temperature

Valid provided that electrodes are kept at ambient temperature

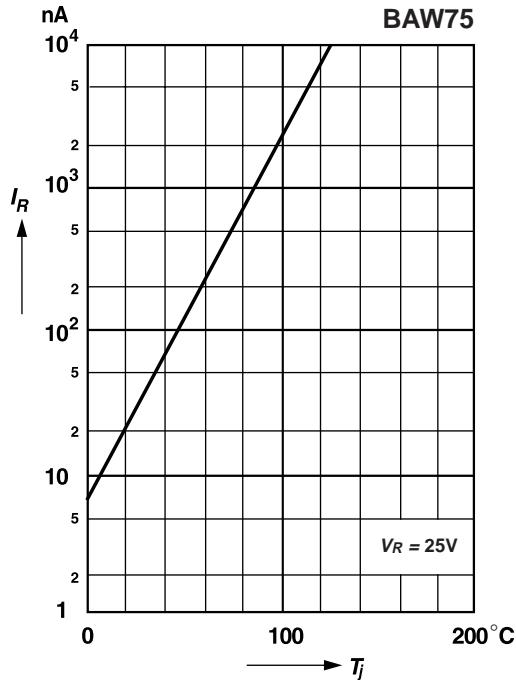


Relative capacitance
versus reverse voltage

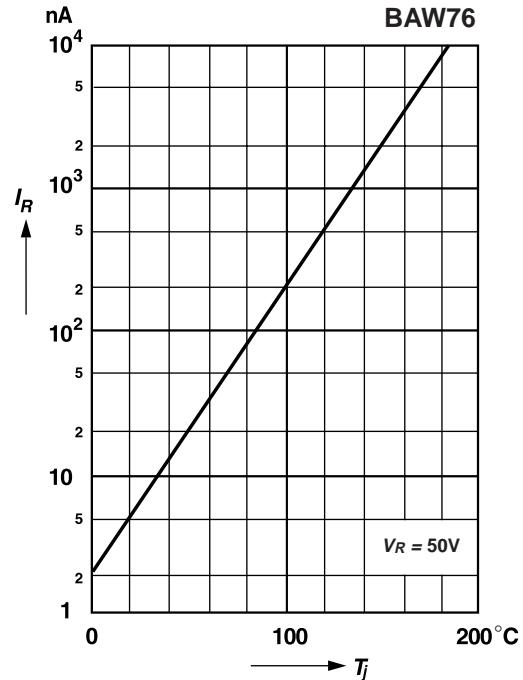


RATINGS AND CHARACTERISTICS CURVES BAW75, BAW76

Leakage current
versus junction temperature



Leakage current
versus junction temperature



Admissible repetitive peak forward current versus pulse duration

For conditions, see footnote in table "Absolute Maximum Ratings"

